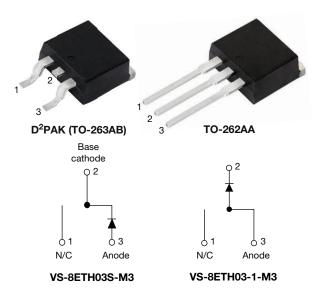
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VS-8ETH03S-M3, VS-8ETH03-1-M3

Vishay Semiconductors

Hyperfast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS					
I _{F(AV)}	8 A				
V _R	300 V				
V _F at I _F	0.83 V				
t _{rr}	35 ns				
T _J max.	175 °C				
Package	D ² PAK (TO-263AB), TO-262AA				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Repetitive peak reverse voltage	V _{RRM}		300	V	
Average rectified forward current	I _{F(AV)}	T _C = 155 °C	8	٨	
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	100	A	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPEC	ECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-		
Forward voltage	V _F	I _F = 8 A	-	1.0	1.25	- μA	
Forward voltage	۷F	I _F = 8 A, T _J = 125 °C	-	0.83	1.00		
Deverse leekerse eurrent		$V_{R} = V_{R}$ rated	-	0.02	20		
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6.0	200	μΑ	
Junction capacitance	CT	V _R = 300 V	-	31	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



COMPLIANT HALOGEN



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DYNAMIC RECOVERY CH	IARACTEF	RISTICS ($T_C = 28$	5 °C unless otherw	vise spec	ified)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A$, $dI_F/dt = -$	50 A/µs, V _R = 30 V	-	-	35	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	27	-	ns
		T _J = 125 °C		-	40	-	
Peak resource surrent		T _J = 25 °C	I _F = 8 A dI _F /dt = - 200 A/μs	-	2.2	-	٨
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 200 \text{ V}$	-	5.3	-	A
	0	T _J = 25 °C		-	30	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	106	-	no

THERMAL - MECHANICA		ICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.45	2.5	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.2	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D ² PAK (TO-263AB)	8ETH03S			
Marking device		Case style TO-262		8ETH	103-1	

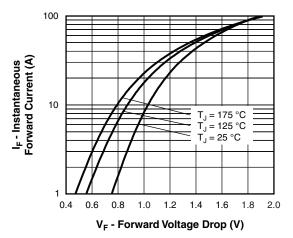


Fig. 1 - Typical Forward Voltage Drop Characteristics

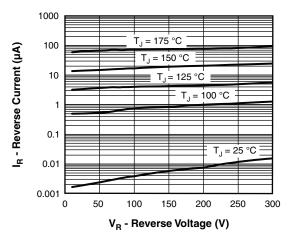


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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VS-8ETH03S-M3, VS-8ETH03-1-M3

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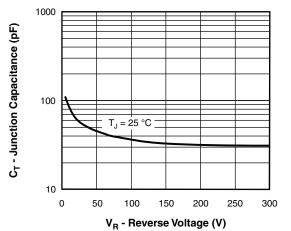


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

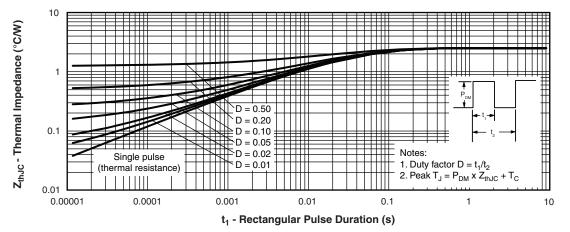


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

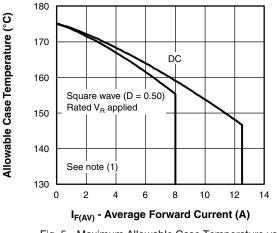
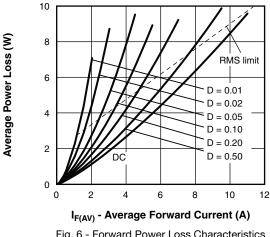


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



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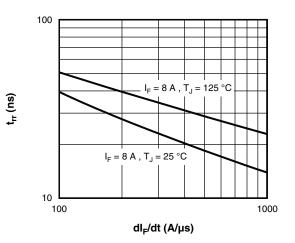
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VS-8ETH03S-M3, VS-8ETH03-1-M3

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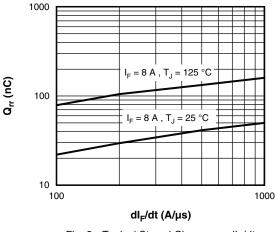


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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$





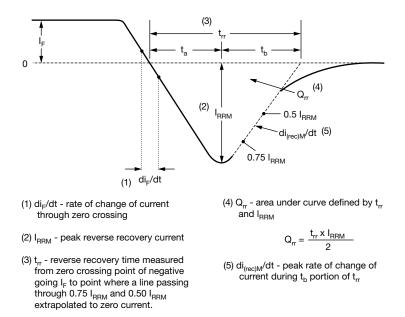
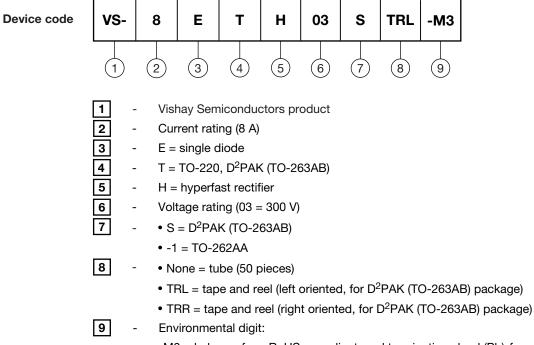


Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164			
Dimensions	TO-262AA	www.vishay.com/doc?96165			
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444			
Fart marking information	TO-262AA <u>www.vishay.com/doc?95443</u>	www.vishay.com/doc?95443			
Packaging information		www.vishay.com/doc?96424			

Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	SYMBOL MILLIMETERS INCHES				NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
		MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

1

Document Number: 96164

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Outline Dimensions



Vishay Semiconductors

TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89 0.020 0.035		4	
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis of the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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